STL9P2UH7

P-channel 20 V, 0.0195 Ω typ., 9 A STripFET™ H7 Power MOSFET in a PowerFLAT™ 3.3x3.3 package

Datasheet - production data

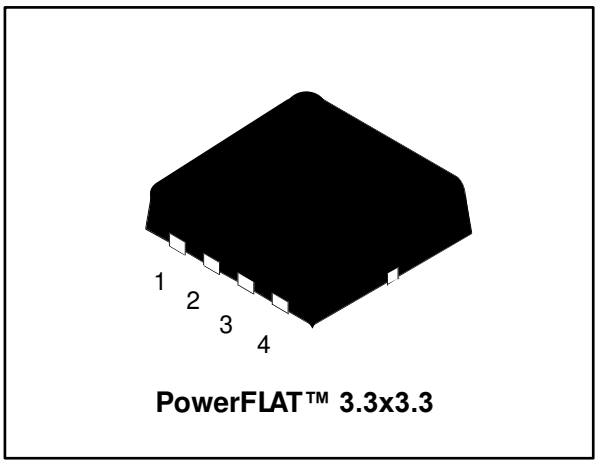
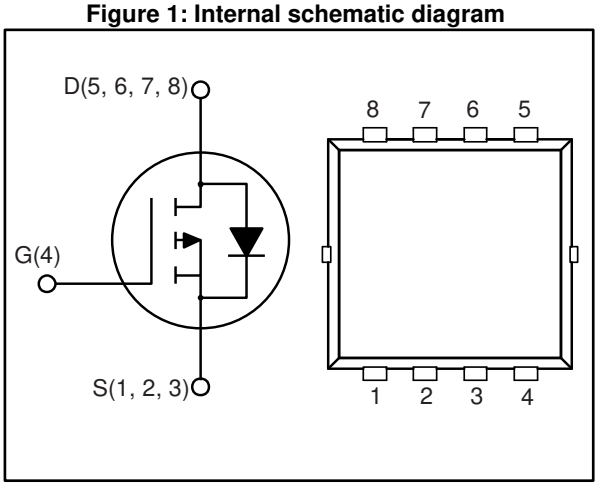


Figure 1: Internal schematic diagram



- Very low on-resistance
- Very low capacitance and gate charge
- High avalanche ruggedness

Applications

- Switching applications

Description

This P-channel Power MOSFET utilizes the STripFET H7 technology with a trench gate structure combined with extremely low on-resistance. The device also offers ultra-low capacitances for higher switching frequency operations.

Table 1: Device summary

Order code	Marking	Package	Packaging
STL9P2UH7	9P2H7	PowerFLAT™ 3.3x3.3	Tape and reel

For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

Features

Order code	V_{DS}	$R_{DS(on)}$max	I_D
STL9P2UH7	20 V	0.0225 Ω @ 4.5 V	9 A

This is information on a product in full production.

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage	20	V
V_{GS}	Gate-source voltage	± 8	V
I_D (1)	Drain current (continuous) at T_{pcb}= 25 °C	9	A
I_D (1)	Drain current (continuous) at T_{pcb}= 100 °C	5.9	A
I_{DM} (2)	Drain current (pulsed)	36	A
P_{TOT} (1)	Total dissipation at T_{pcb}= 25 °C	2.9	W
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	°C

Notes:

(1)The value is rated according to R thj-pcb

(2)Pulse width limited by safe operating area

Table 3: Thermal resistance

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	2.5	°C/W
$R_{thj\text{-}pcb}$ (1)	Thermal resistance junction-pcb	42	°C/W

Notes:

(1)When mounted on FR-4 board of 1inch², 2oz Cu, t < 10 sec.



For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

2 Electrical characteristics

(T_C= 25 °C unless otherwise specified)

Table 4: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	V_{GS} = 0, I_D = 250 µA	20			V
I_{DSS}	Zero gate voltage drain current	V_{GS}= 0, V_{DS} = 20 V			1	µA
I_{GSS}	Gate-body leakage current	V_{DS} = 0, V_{GS} = ± 5 V			± 5	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	0.4		1	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS}= 4.5 V, I_D= 4.5 A		0.0195	0.0225	Ω
		V_{GS} = 2.5 V, I_D = 4.5 A		0.02	0.025	Ω
		V_{GS} = 1.8 V, I_D = 4.5 A		0.036	0.043	Ω
		V_{GS} = 1.5 V, I_D = 4.5 A		0.05	0.085	Ω

Table 5: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0, V_{DS} = 16 V, f = 1 MHz	-	2390	-	pF
C_{oss}	Output capacitance		-	220	-	pF
C_{rss}	Reverse transfer capacitance		-	188	-	pF
Q_g	Total gate charge	V_{DD} = 15 V, I_D = 9 A, V_{GS} = 4.5 V	-	22	-	nC
Q_{gs}	Gate-source charge		-	4.2	-	nC
Q_{gd}	Gate-drain charge		-	3.6	-	nC

Table 6: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 16 V, I_D = 9 A, R_G = 1 Ω, V_{GS} = 4.5 V	-	12.5	-	ns
t_r	Rise time		-	30.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	128	-	ns
t_f	Fall time		-	84.5	-	ns

Table 7: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V_{SD} (1)	Forward on voltage	V_{GS}= 0, I_{SD}= 1 A	-	-	1	V
t_{rr}	Reverse recovery time	V_{DD}= 16 V di/dt = 100 A/µs, I_{SD}= 1 A	-	15.8		ns
Q_{rr}	Reverse recovery charge		-	5.9		nC
I_{RRM}	Reverse recovery current		-	0.7		A

Notes:

(1)Pulsed: pulse duration = 300 µs, duty cycle 1.5%



For the P-channel Power MOSFET the actual polarity of the voltages and the current must be reversed.

2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

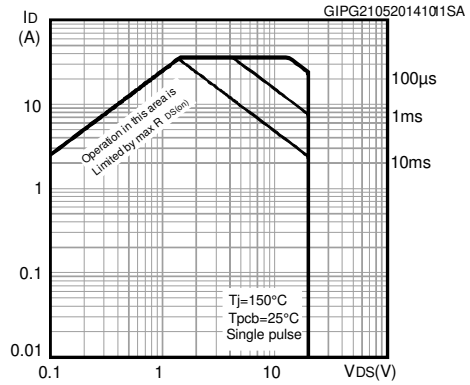


Figure 3: Thermal impedance

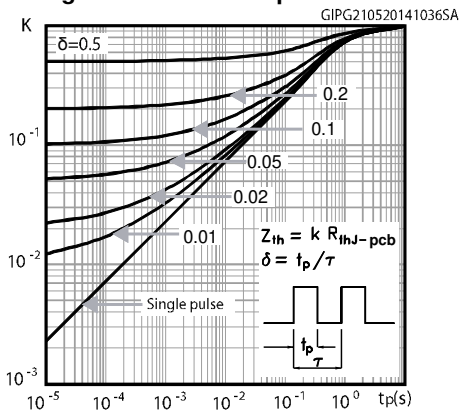


Figure 4: Output characteristics

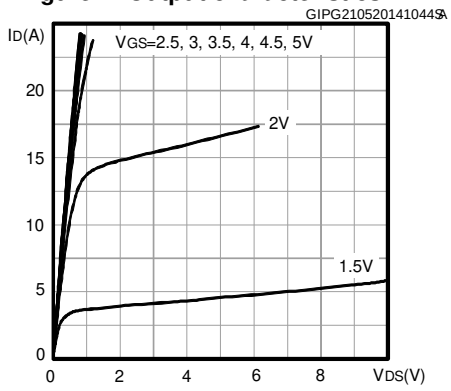


Figure 5: Transfer characteristics

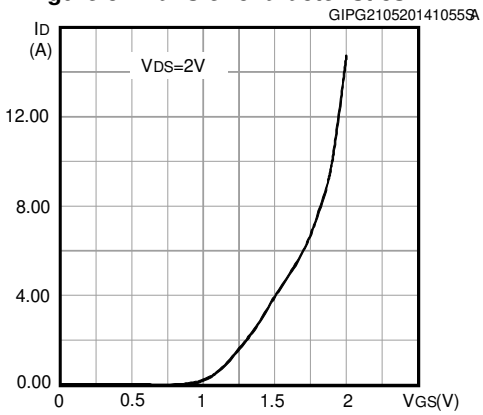


Figure 6: Gate charge vs gate-source voltage

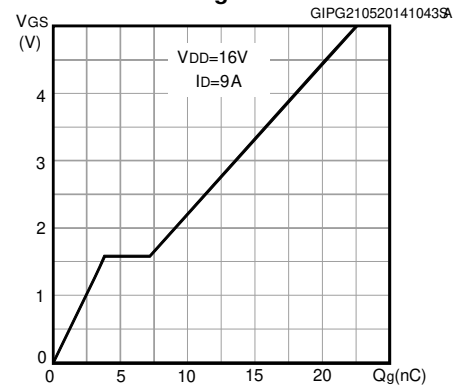


Figure 7: Static drain-source on-resistance

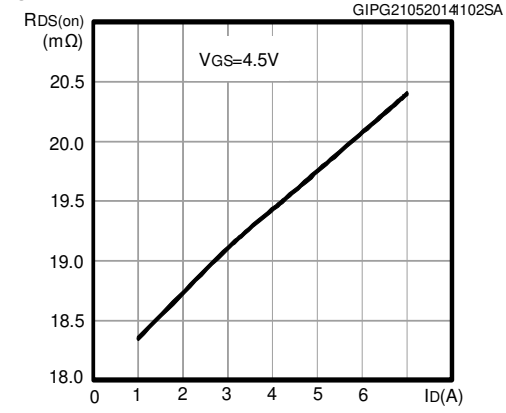


Figure 8: Capacitance variations

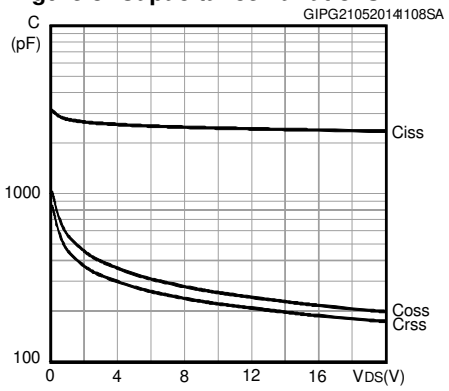


Figure 9: Normalized gate threshold voltage vs temperature

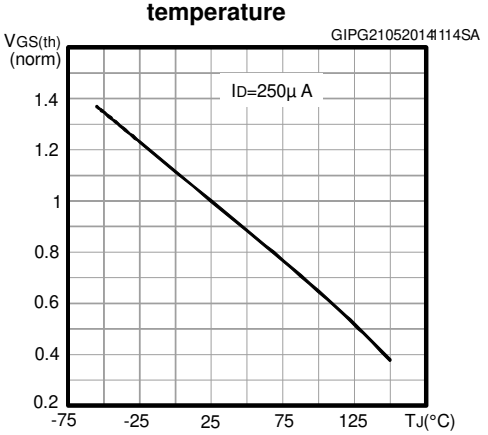


Figure 10: Normalized on-resistance vs temperature

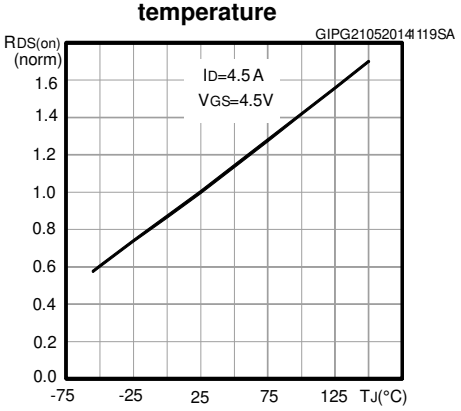


Figure 11: Normalized V(BR)DSS vs temperature

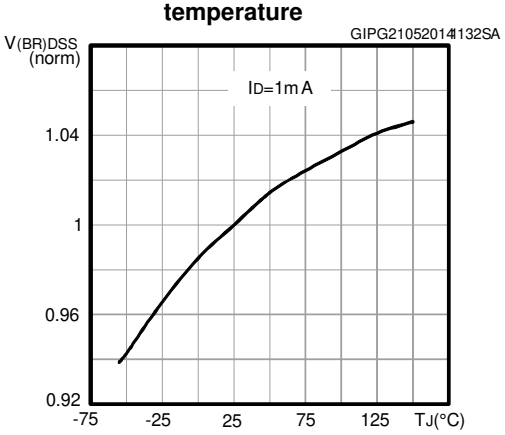
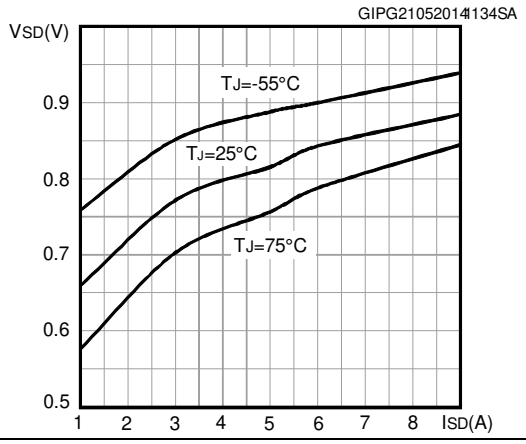


Figure 12: Source-drain diode forward characteristics



3 Test circuits

Figure 13: Switching times test circuit for resistive load

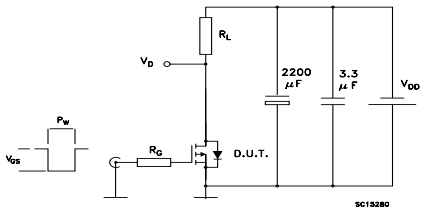


Figure 14: Gate charge test circuit

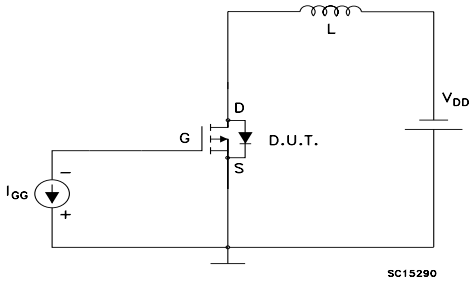
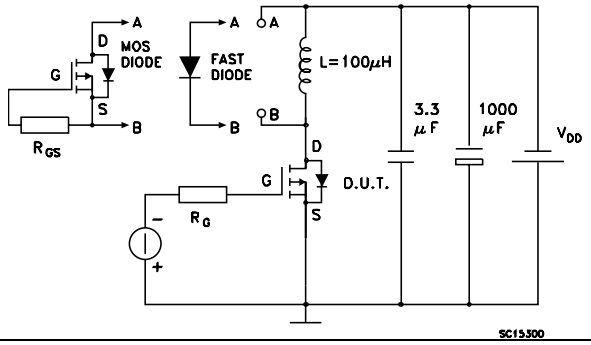


Figure 15: Test circuit for inductive load switching and diode recovery times



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 PowerFLAT™ 3.3 x 3.3 package mechanical data

Figure 16: PowerFLAT™ 3.3 x 3.3 drawing

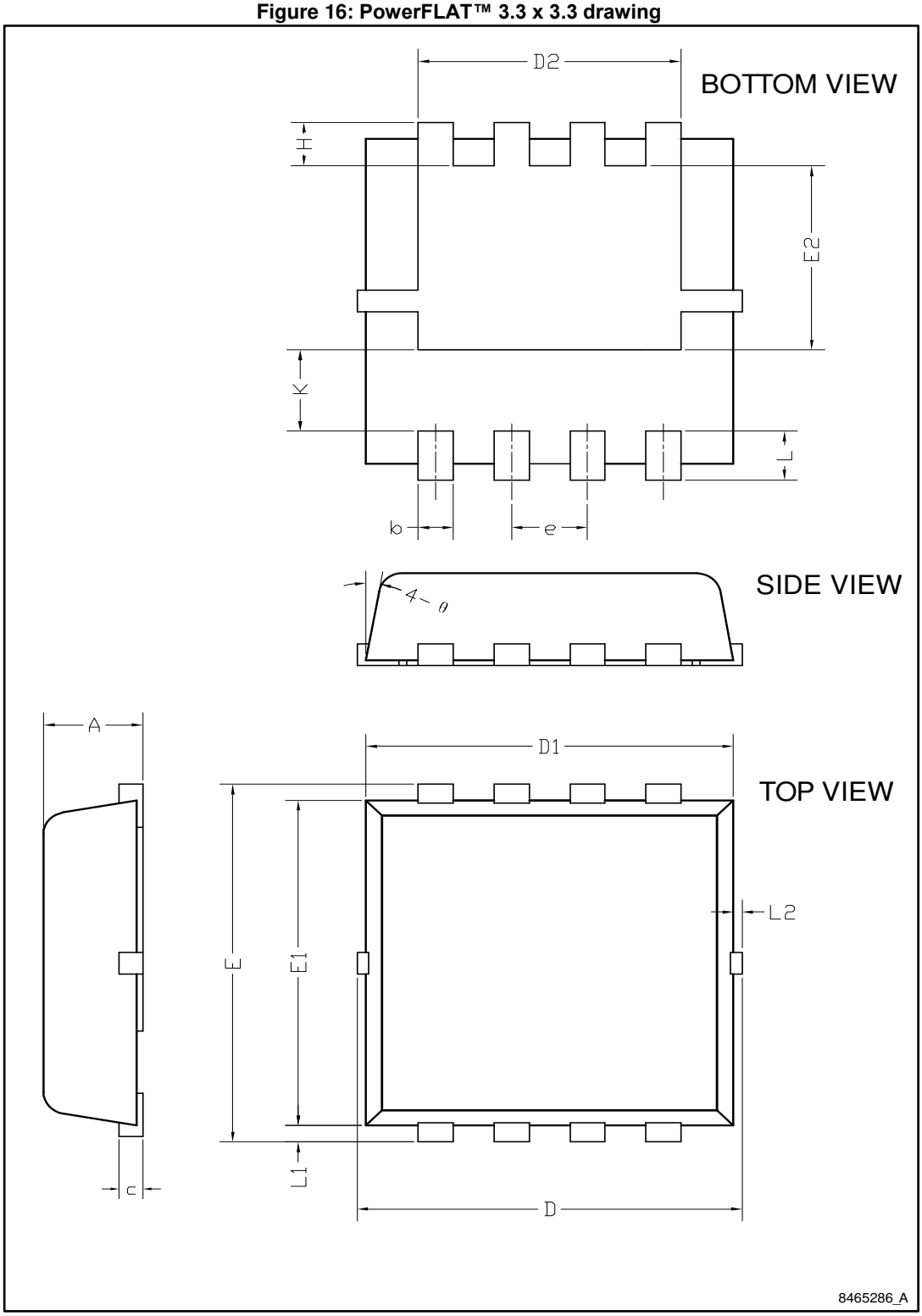
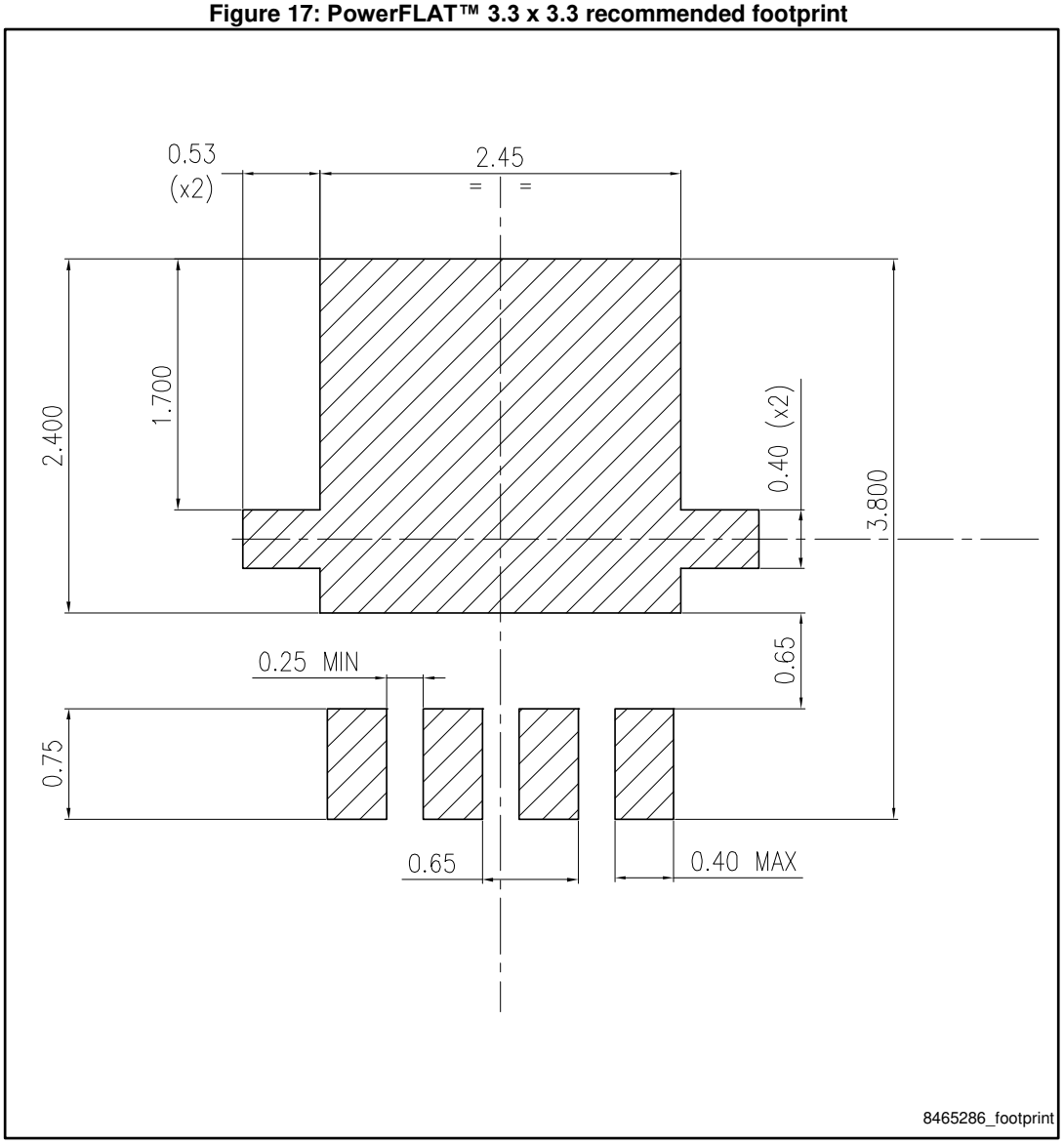


Table 8: PowerFLAT™ 3.3 x 3.3 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.70	0.80	0.90
b	0.25	0.30	0.39
c	0.14	0.15	0.20
D	3.10	3.30	3.50
D1	3.05	3.15	3.25
D2	2.15	2.25	2.35
e	0.55	0.65	0.75
E	3.10	3.30	3.50
E1	2.90	3.00	3.10
E2	1.60	1.70	1.80
H	0.25	0.40	0.55
K	0.65	0.75	0.85
L	0.30	0.45	0.60
L1	0.05	0.15	0.25
L2			0.15
J	8°	10°	12°

Figure 17: PowerFLAT™ 3.3 x 3.3 recommended footprint



5 Revision history

Table 9: Document revision history

Date	Revision	Changes
26-Aug-2013	1	First release.
04-Jun-2014	2	Document status promoted from preliminary data to production data Modified: title Modified: $R_{DS(on)}$ max value in cover page Modified: $R_{DS(on)}$ (typical and maximum) values in *Table 4: "On /off states"* Modified: the entire typical values in *Table 5: "Dynamic", Table 6: "Switching times"* and *Table 7: "Source drain diode"* Added: *Section 8.1: "Electrical characteristics (curves)"* Minor text changes
21-Oct-2014	3	Updated the title, the features and the description in cover page. Updated *Figure 1: "Internal schematic diagram"*. Minor text changes.

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